

# Yoshihiro Kokubun

## List of Publications by Year in descending order

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Version: 2024-02-01

19  
papers

1,134  
citations

840776

11  
h-index

888059

17  
g-index

19  
all docs

19  
docs citations

19  
times ranked

1183  
citing authors

| #  | ARTICLE   | IF  | CITATIONS |
|----|---|-----|-----------|
| 1  | Sol-gel prepared $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> thin films for ultraviolet photodetectors. Applied Physics Letters, 2007, 90, 031912.   | 3.3 | 376       |
| 2  | Enhancement of responsivity in solar-blind $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> photodiodes with a Au Schottky contact fabricated on single crystal substrates by annealing. Applied Physics Letters, 2009, 94, .                             | 3.3 | 217       |
| 3  | Deep ultraviolet photodiodes based on $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> /SiC heterojunction. Applied Physics Letters, 2013, 103, .   | 3.3 | 193       |
| 4  | All-oxide p-n heterojunction diodes comprising p-type NiO and n-type $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> . Applied Physics Express, 2016, 9, 091101.   | 2.4 | 137       |
| 5  | Sol-gel prepared (Ga <sub>1-x</sub> In <sub>x</sub> ) <sub>2</sub> O <sub>3</sub> thin films for solar-blind ultraviolet photodetectors. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1741-1745.                              | 1.8 | 68        |
| 6  | $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> /p-type 4H-SiC Heterojunction Diodes and Applications to Deep-UV Photodiodes. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1700796.  | 1.8 | 24        |
| 7  | Cross-sectional TEM imaging of $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> thin films formed on c-plane and a-plane sapphire substrates. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 1738-1744.                         | 1.8 | 21        |
| 8  | NiO films grown epitaxially on MgO substrates by sol-gel method. Thin Solid Films, 2016, 601, 76-79.  | 1.8 | 20        |
| 9  | The orientational relationship between monoclinic $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> and cubic NiO. Journal of Crystal Growth, 2016, 445, 73-77.  | 1.5 | 18        |
| 10 | Crystal orientations of $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> thin films formed on m-plane and r-plane sapphire substrates. Physica Status Solidi (B): Basic Research, 2015, 252, 612-620.   | 1.5 | 13        |
| 11 | Crystal orientations of $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> thin films formed on c-plane GaN substrate. Physica Status Solidi (B): Basic Research, 2016, 253, 1217-1221.   | 1.5 | 11        |
| 12 | Cross-sectional TEM imaging of $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> thin films formed on c-plane and a-plane sapphire substrates (Phys. Status Solidi A 91(2013)). Physica Status Solidi (A) Applications and Materials Science, 2013, 210, . | 1.8 | 10        |
| 13 | Crystal Orientation of Cubic NiO Thin Films Formed on Monoclinic $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> Substrates. Physica Status Solidi (B): Basic Research, 2020, 257, 1900669.  | 1.5 | 9         |
| 14 | Large Voltage Response of Novel Diode of Pt-TiO <sub>2</sub> -SiC Structure to Hydrogen Gas. Electrochemistry, 2003, 71, 394-397.   | 1.4 | 7         |
| 15 | Electrical Conductivity Studies in Sol-Gel-Derived Li-Doped NiO Epitaxial Thin Films. Physica Status Solidi (B): Basic Research, 2020, 257, 2000330.  | 1.5 | 5         |
| 16 | Hydrogen Gas Response of Pt-thin SiO <sub>2</sub> -SiC Schottky Diode in the Presence of Oxygen. Electrochemistry, 2002, 70, 174-177.   | 1.4 | 3         |
| 17 | Magnesium Diffusion from MgO Substrates in Sol-Gel-Derived NiO Epitaxial Films: Effects of Heat Treatment Temperature and Li-Doping. Physica Status Solidi (B): Basic Research, 2021, 258, 2100230.   | 1.5 | 2         |
| 18 | Crystal orientations of $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> thin films formed on n-plane sapphire substrates. Physica Status Solidi (B): Basic Research, 2015, 252, 2117-2122.   | 1.5 | 0         |

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 19 | Electrical Properties of Beta-Irondisilicide/Germanium Heterojunctions. Materials Research Society Symposia Proceedings, 2002, 722, 931. | 0.1 | 0         |